

# HD74LV1GW07A

# **Dual Buffer Open Drain**

REJ03D0076-0300 Rev.3.00 Sep 08, 2006

#### **Description**

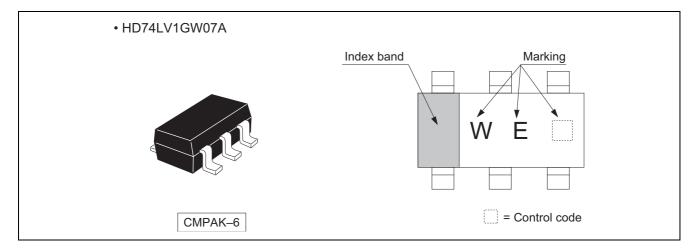
The HD74LV1GW07A has dual buffer open drain in a 6 pin package. Low voltage and high-speed operation is suitable for the battery powered products (e.g., notebook computers), and the low power consumption extends the battery life.

#### **Features**

- The basic gate function is lined up as Renesas uni logic series.
- Supplied on emboss taping for high-speed automatic mounting.
- Supply voltage range: 1.65 to 5.5 V
   Operating temperature range: -40 to +85°C
- $\begin{array}{l} \bullet \quad \mbox{All inputs $V_{IH}$ (Max.) = 5.5 V (@V_{CC} = 0 \ V \ to 5.5 \ V)$} \\ \mbox{All outputs $V_O$ (Max.) = 5.5 V (@V_{CC} = 0 \ V, \ Output: Z)$} \\ \end{array}$
- Output current 6 mA (@ $V_{CC} = 3.0 \text{ V}$  to 3.6 V), 12 mA (@ $V_{CC} = 4.5 \text{ V}$  to 5.5 V)
- All the logical input has hysteresis voltage for the slow transition.
- Ordering Information

Part Name	Package Type	Package Code (Previous Code)	Package Abbreviation	Taping Abbreviation (Quantity)
HD74LV1GW07ACME	CMPAK-6 pin	PTSP0006JA-A (CMPAK-6V)	СМ	E (3,000 pcs / Reel)

#### **Outline and Article Indication**



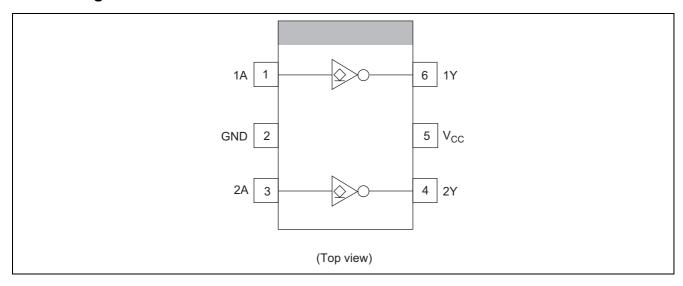
#### **Function Table**

Input A	Output Y
Н	Z
L	L

H : High level L : Low level

Z: High impedance

### **Pin Arrangement**



# **Absolute Maximum Ratings**

Item	Symbol	Ratings	Unit	Test Conditions
Supply voltage range	Vcc	-0.5 to 7.0	V	
Input voltage range *1	Vı	-0.5 to 7.0	V	
Output voltage range *1, 2	\/	-0.5 to V <sub>CC</sub> + 0.5	V	Output : L
	Vo	-0.5 to 7.0	V	V <sub>CC</sub> : OFF or Output : Z
Input clamp current	I <sub>IK</sub>	-20	mA	V <sub>I</sub> < 0
Output clamp current	lok	-50	mA	V <sub>O</sub> < 0
Continuous output current	I <sub>O</sub>	±25	mA	$V_O = 0$ to $V_{CC}$
Continuous current through Vcc or GND	I <sub>CC</sub> or I <sub>GND</sub>	±50	mA	
Maximum power dissipation at Ta = 25°C (in still air) *3	P <sub>T</sub>	200	mW	
Storage temperature	Tstg	-65 to 150	°C	

Notes: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore no two of which may be realized at the same time.

- 1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
- 2. This value is limited to 5.5 V maximum.
- 3. The maximum package power dissipation was calculated using a junction temperature of 150°C.

# **Recommended Operating Conditions**

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage range	V <sub>CC</sub>	1.65	5.5	V	
Input voltage range	VI	0	5.5	V	
Output voltage range	Vo	0	V <sub>CC</sub>	V	
Output ourrant		_	1		V <sub>CC</sub> = 1.65 to 1.95 V
	I <sub>OL</sub>	_	2	mA	$V_{CC} = 2.3 \text{ to } 2.7 \text{ V}$
Output current		_	6	IIIA	$V_{CC} = 3.0 \text{ to } 3.6 \text{ V}$
		_	12		$V_{CC} = 4.5 \text{ to } 5.5 \text{ V}$
		0	300		V <sub>CC</sub> = 1.65 to 1.95 V
Input transition rise or fall rate	Δt / Δν	0	200	ns / V	$V_{CC} = 2.3 \text{ to } 2.7 \text{ V}$
Input transition rise or fall rate	Δι / Δν	0	100	115 / V	$V_{CC} = 3.0 \text{ to } 3.6 \text{ V}$
		0	20		$V_{CC} = 4.5 \text{ to } 5.5 \text{ V}$
Operating free-air temperature	Ta	-40	85	°C	

Note: Unused or floating inputs must be held high or low.

### **Electrical Characteristic**

 $Ta = -40 \text{ to } 85^{\circ}\text{C}$ 

Item	Symbol	V <sub>CC</sub> (V) *1	Min	Тур	Max	Unit	Test Condition
		1.65 to 1.95	V <sub>CC</sub> ×0.75	_	_		
	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	2.3 to 2.7	V <sub>CC</sub> ×0.7	_	_		
	V <sub>IH</sub>	3.0 to 3.6	V <sub>CC</sub> ×0.7	_	_		
Input voltage		4.5 to 5.5	V <sub>CC</sub> ×0.7	_	_	V	
Input voltage		1.65 to 1.95	_	_	V <sub>CC</sub> ×0.25	V	
	\/	2.3 to 2.7	_	_	V <sub>CC</sub> ×0.3		
	V <sub>IL</sub>	3.0 to 3.6	_	_	V <sub>CC</sub> ×0.3		
		4.5 to 5.5	_	_	V <sub>CC</sub> ×0.3		
		1.8	_	0.25	_		
Hysteresis voltage	\/	2.5	_	0.30	_	V	$V_T^+ - V_T^-$
	V <sub>H</sub>	3.3	_	0.35	_	V	$V_T - V_T$
		5.0	_	0.45	_		
		Min to Max	_	_	0.1		$I_{OL} = 50 \mu A$
		1.65	_	_	0.3		I <sub>OL</sub> = 1 mA
Output voltage	$V_{OL}$	2.3	_	_	0.4	V	I <sub>OL</sub> = 2 mA
		3.0	_	_	0.44		I <sub>OL</sub> = 6 mA
		4.5	_	_	0.55		I <sub>OL</sub> = 12 mA
Input current	I <sub>IN</sub>	0 to 5.5	_	_	±1	μΑ	V <sub>IN</sub> = 5.5 V or GND
Off state	1	Min to Max			±5	^	V - F F V or CND
output current	l <sub>OZ</sub>	WIII to Wax			±Ο	μΑ	$V_0 = 5.5 \text{ V or GND}$
Quiescent	I <sub>CC</sub>	5.5			10	μΑ	$V_{IN} = V_{CC}$ or GND,
supply current	100	5.5			10	μΛ	$I_{O} = 0$
Output leakage	I <sub>OFF</sub>	0	_	_	5	μΑ	$V_{IN}$ or $V_O = 0$ to 5.5 V
current		_					-
Input capacitance	C <sub>IN</sub>	3.3	_	3.0	_	pF	$V_{IN} = V_{CC}$ or GND

Note: For conditions shown as Min or Max, use the appropriate values under recommended operating conditions.

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# **Switching Characteristics**

 $V_{CC}=1.8\pm0.15\ V$ 

Item	Symbol	Ta = 25°C			Ta = -40 to 85°C		Unit	Test	FROM	ТО
item	Syllibol	Min	Тур	Max	Min	Max	Onit	Conditions	(Input)	(Output)
Propagation	t <sub>ZL</sub>	_	12.6	22.0	1.0	24.0	20	$C_L = 15  pF$	۸	V
delay time	$t_{LZ}$		19.7	33.0	1.0	36.0	ns	$C_L = 50 pF$	A	ī

 $V_{CC}=2.5\pm0.2~V$ 

Item	Symbol	Ta = 25°C			Ta = -40 to 85°C		Unit	Test	FROM	ТО
		Min	Тур	Max	Min	Max	Oill	Conditions	(Input)	(Output)
Propagation	t <sub>ZL</sub>	_	7.0	11.7	1.0	14.0	nc	$C_L = 15 pF$	٨	<b>V</b>
delay time	$t_{LZ}$	_	10.5	15.5	1.0	18.0	ns	$C_L = 50 pF$	A	ı

 $V_{CC}=3.3\pm0.3\ V$ 

Item Sy	Symbol	Ta = 25°C			Ta = -40 to 85°C		Unit	Test	FROM	ТО
	Syllibol	Min	Тур	Max	Min	Max	Offic	Conditions	(Input)	(Output)
Propagation	t <sub>ZL</sub>	_	5.0	7.1	1.0	8.5	nc	C <sub>L</sub> = 15 pF	۸	V
delay time	$t_{LZ}$	_	7.5	10.6	1.0	12.0	ns	$C_L = 50 pF$	A	ı

 $V_{CC}=5.0\pm0.5~V$ 

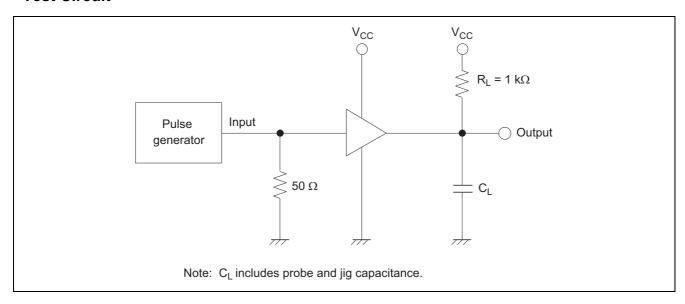
Item Symbol		Ta = 25°C			Ta = -40 to 85°C		Unit	Test	FROM	ТО
iteiii	Syllibol	Min	Тур	Max	Min	Max	Onit	Conditions	(Input)	(Output)
Propagation	t <sub>ZL</sub>		3.8	5.5	1.0	6.5	nc	C <sub>L</sub> = 15 pF	۸	V
delay time	$t_{LZ}$		5.3	7.5	1.0	8.5	ns	C <sub>L</sub> = 50 pF	A	ī

# **Operating Characteristics**

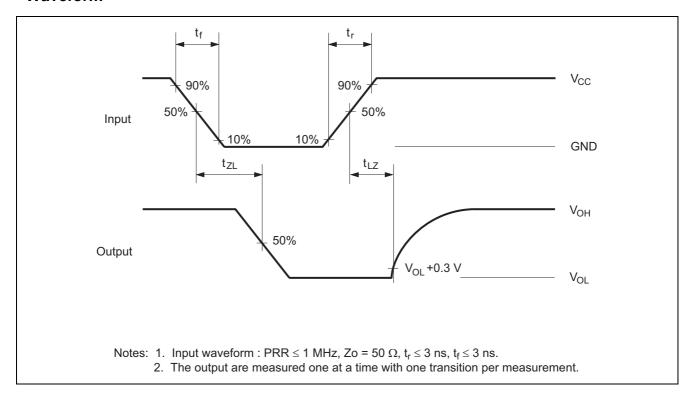
 $C_L = 50 \text{ pF}$ 

Item	Symbol	V <sub>cc</sub> (V)	7	Га = 25°C	;	Unit	Test Conditions	
	Symbol	VCC (V)	Min	Тур	Max	Unit	rest Conditions	
Power dissipation	C	3.3	_	8.5	_	pF	f = 10 MHz	
capacitance	$C_{PD}$	5.0	_	10.0	_	рг		

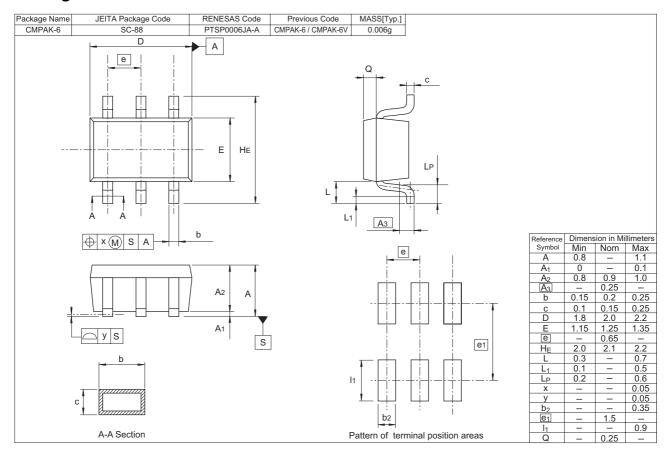
### **Test Circuit**



#### Waveform



# **Package Dimensions**



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